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		Applicant(s) Khan et al.				
		Filing Date September 27, 2001	Group Art Unit 2814			
U.S. PATENT DOCUMENTS						
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CLASS	SUBCLASS	FILING DATE IF APPROPRIATE				
FOREIGN PATENT DOCUMENTS						
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translated YES NO
OTHER DOCUMENTS <small>(Including Author, Title, Date, Pertinent Pages, Etc.)</small>						
LP	'The Influence of the Strain-Induced Electric Field on the Charge Distribution in GaN-AlN-GaN Structures' A. D. Bykovski et al., Journal of Applied Physics, Vol. 74, No. 11, December 1, 1993, pp.6734-6739.					
LP	'Pyroelectricity in Gallium Nitride Thin Films,' A. D. Bykovski et al., Applied Physics Letters, Vol. 69, No. 21, November 18, 1996, pp. 3254-3256.					
EXAMINER LONG PHAM		DATE CONSIDERED 11/1/03				
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EXAMINER REVIEWED LP	OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
	"Piezoelectric and Piezoelectric Properties of GaN-Based Materials," M. S. Shur et al., MRS Internet J. Nitride Semicond. Res. 4S1, G1.6 (1999), pp. 1-12.		
	"Piezoeffect and Gate Current in AlGaN/GaN High Electron Mobility Transistors," R. Gaska et al., Applied Physics Letters, Vol. 71, No. 25, December 22, 1997, pp. 3673-3675.		
	"Two-Dimensional Electron-Gas Density in Al _x GaN/GaN Heterostructure Field-Effect Transistors," N. Maeda et al., Applied Physics Letters, Vol. 73, No. 13, September 28, 1998, pp. 1856-1858.		
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	"Ferroelectric Semiconductors," V. M. Fridkin, Russia (1976), p. 90 (pp. 64-65 in English version).		
	"Lattice and Energy Band Engineering in AlInGaN/GaN Heterostructures," M. A. Khan et al., Applied Physics Letters, Vol. 76, No. 9, February 28, 2000, pp. 1161-1163.		
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EXAMINER LP	"Current/Voltage Characteristic Collapse in AlGaN/GaN Heterostructure Insulated Gate Field Effect Transistors at High Drain Bias," M. A. Khan et al., Electronic Letters, Vol. 30, No. 25, December 8, 1994, pp. 2175-2176. <i>RECEIVED - 11/1/03</i>		
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